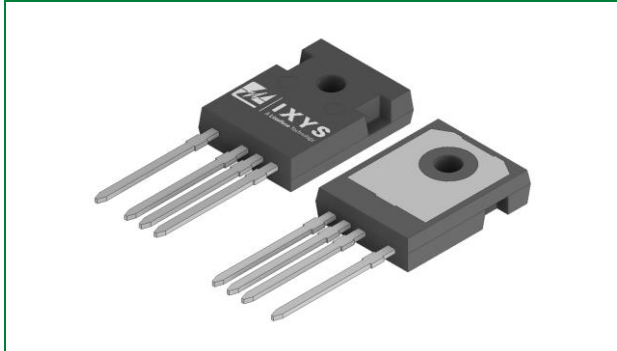


LSIC1MO120G0120
1200 V, 120 mOhm N-Channel SiC MOSFET

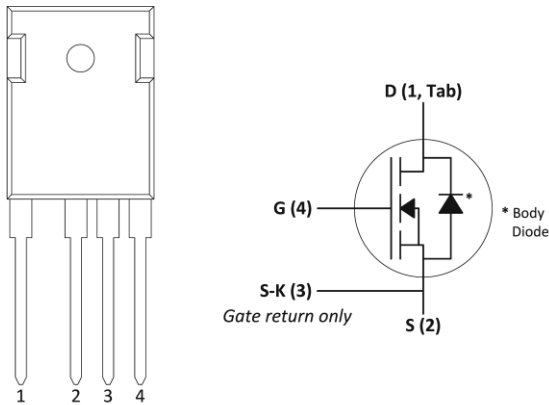


Agency Approvals and Environmental

Environmental Approvals



Circuit Diagram



Product Summary

Characteristic	Value	Unit
V_{DS}	1200	V
Typical $R_{DS(ON)}$	120	mOhm
I_D ($T_C \leq 100\text{ }^\circ\text{C}$)	18	A

Features

- Optimized for high-frequency, high-efficiency applications
- Extremely low gate charge and output capacitance
- Low gate resistance for high-frequency switching
- Normally-off operations at all temperatures
- Ultra-low on-resistance
- Optimized package with separate driver source pin

Applications

- High-frequency applications
- Solar Inverters
- Switch Mode Power Supplies
- UPS
- Motor Drives
- High Voltage DC/DC Converters
- Battery Chargers
- Induction Heating

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1. Maximum Ratings

Characteristic	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}	$V_{GS} = 0\text{ V}$	1200	V
Continuous Drain Current	I_D	$V_{GS} = 20\text{ V}, T_C = 25\text{ }^\circ\text{C}$	27	A
		$V_{GS} = 20\text{ V}, T_C = 100\text{ }^\circ\text{C}$	18	
Pulsed Drain Current ¹	$I_{D(pulse)}$	$T_C = 25\text{ }^\circ\text{C}$	60	A
Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}, T_J = 175\text{ }^\circ\text{C}$	156	W
Gate-Source Voltage	$V_{GS,MAX}$	Absolute maximum values – Steady state	-6 to +22	V
	$V_{GS,OP,TR}$ ²	Transient, $t_{transient} < 300\text{ nsec}$	-10 to +25	
	$V_{GS,OP}$ ³	Recommended DC operating values	-5 to +20	
Operating Junction Temperature	T_J	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}	-	-55 to +150	$^\circ\text{C}$
Lead Temperature for Soldering	T_{sold}	-	260	$^\circ\text{C}$
Mounting Torque	M_D	M3 or 6-32 screw	1.0	Nm
			8.8	in-lb

Footnote 1: Pulse width limited by $T_{J,MAX}$

Footnote 2: See Figure 21 for further information

Footnote 3: MOSFET can operate with $V_{GS(OFF)} = 0\text{ V}$. $V_{GS(OFF)} = -5\text{ V}$ provides added noise margin and faster turn-off speed

2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, junction-to-case	$R_{th,JC,MAX}$	0.96	$^\circ\text{C/W}$
Maximum Thermal Resistance, junction-to-ambient	$R_{th,JA,MAX}$	40	$^\circ\text{C/W}$

3. Electrical Characteristics

3.1. Static Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}$	-	<1	100	μA
		$V_{DS} = 1200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	<1	-	
Gate Leakage Current	$I_{GSS,F}$	$V_{GS} = 22\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	nA
	$I_{GSS,R}$	$V_{GS} = -6\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D = 14\text{ A}, V_{GS} = 20\text{ V}$	-	120	150	m Ω
		$I_D = 14\text{ A}, V_{GS} = 20\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	170	-	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 7\text{ mA}$	1.8	2.8	4.0	V
		$V_{DS} = V_{GS}, I_D = 7\text{ mA}, T_J = 175\text{ }^\circ\text{C}$	-	1.8	-	
Gate Resistance	R_G	Resonance method, Drain-Source shorted ¹	-	0.8	-	Ω

Footnote 1: For a description of the resonance method for measuring R_G , refer to the JEDEC Standard JESD24-11 test method

3.2. Dynamic Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Turn-On Switching Energy	E_{ON}	$V_{DD} = 800\text{ V}$, $I_D = 14\text{ A}$, $V_{GS} = -5 / +20\text{ V}$, $R_{G,ext} = 2\ \Omega$, $L = 1.4\ \mu\text{H}$, FWD = LSIC2SD120A10	-	68	-	μJ
Turn-Off Switching Energy	E_{OFF}		-	40	-	
Total Per-Cycle Switching Energy	E_{TS}		-	108	-	
Input Capacitance	C_{ISS}	$V_{DD} = 800\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$, $V_{AC} = 25\text{ mV}$	-	1130	-	pF
Output Capacitance	C_{OSS}		-	58	-	
Reverse Transfer Capacitance	C_{RSS}		-	7	-	
COSS Stored Energy	E_{OSS}		-	19	-	
Total Gate Charge	Q_g	$V_{DD} = 800\text{ V}$, $I_D = 14\text{ A}$, $V_{GS} = -5 / +20\text{ V}$	-	63	-	nC
Gate-Source Charge	Q_{gs}		-	21	-	
Gate-Drain Charge	Q_{gd}		-	23	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 800\text{ V}$, $I_D = 14\text{ A}$, $V_{GS} = -5 / +20\text{ V}$, $R_{G,ext} = 2\ \Omega$, $R_L = 56\ \Omega$, Timing relative to V_{DS}	-	11	-	ns
Rise Time	t_r		-	5	-	
Turn-Off Delay Time	$t_{d(off)}$		-	16	-	
Fall Time	t_f		-	8	-	

4. Reverse Diode Characteristics ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Diode Forward Voltage	V_{SD}	$I_S = 7\text{ A}$, $V_{GS} = -5\text{ V}$	-	4.2	-	V
		$I_S = 7\text{ A}$, $V_{GS} = -5\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$	-	3.7	-	
Continuous Diode Forward Current	I_S	$V_{GS} = -5\text{ V}$, $T_C = 25\text{ }^\circ\text{C}$	-	-	26	A
Peak Diode Forward Current ¹	I_{SP}		-	-	60	
Reverse Recovery Time	t_{rr}	$V_{GS} = -5\text{ V}$, $I_S = 14\text{ A}$, $V_R = 800\text{ V}$, $dI/dt = 10.2\text{ A/ns}$	-	8.8	-	ns
Reverse Recovery Charge	Q_{rr}		-	245	-	nC
Peak Reverse Recovery Current	I_{rrm}		-	45	-	A

Footnote 1: Pulse width limited by $T_{J,MAX}$

5. Performance Curves

Figure 1. Maximum Power Dissipation ($T_J = 175\text{ }^\circ\text{C}$)

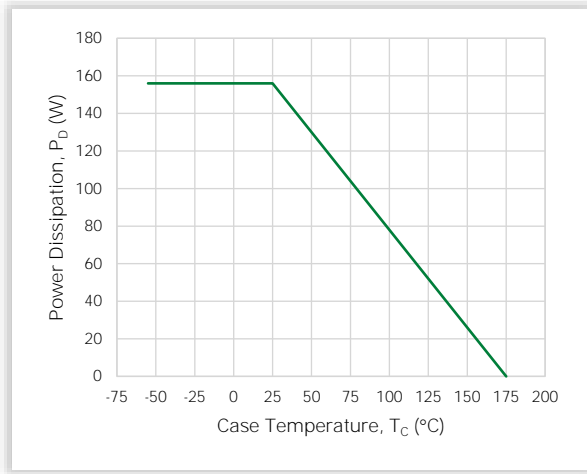


Figure 2. Typical Transfer Characteristics

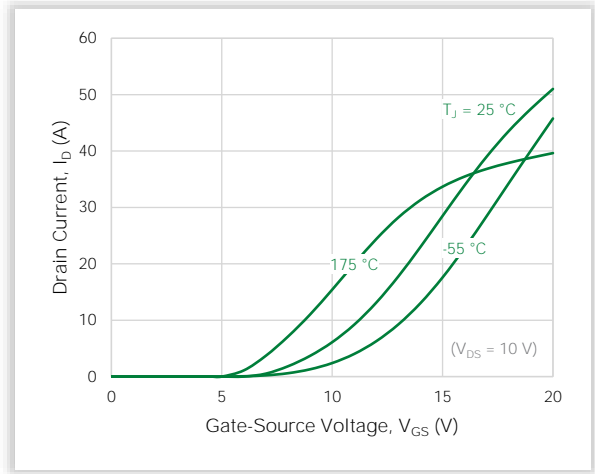


Figure 3. Typical Output Characteristics ($T_J = 25\text{ }^\circ\text{C}$)

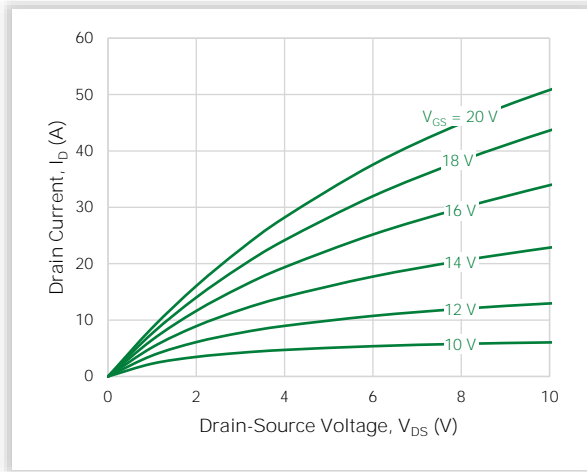


Figure 4. Typical Output Characteristics ($T_J = 175\text{ }^\circ\text{C}$)

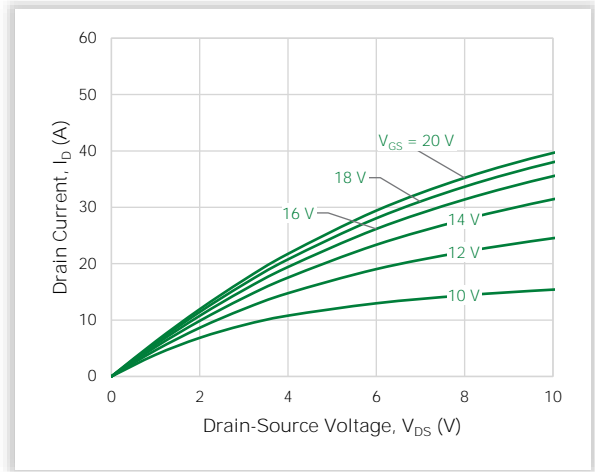


Figure 5. Typical Output Characteristics ($T_J = -55\text{ }^\circ\text{C}$)

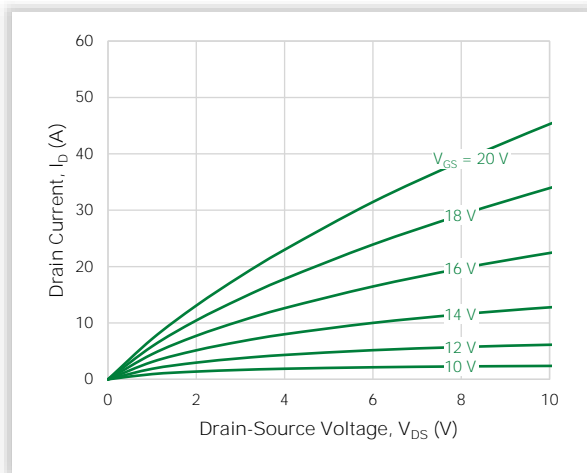


Figure 6. Typical Reverse Conduction Characteristics ($T_J = 25\text{ }^\circ\text{C}$)

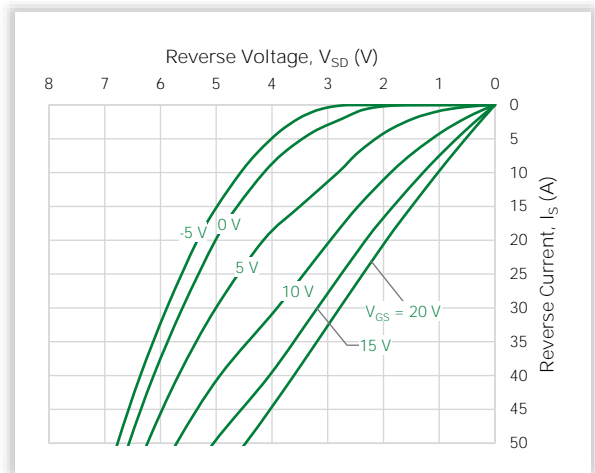


Figure 7. Typical Reverse Conduction Characteristics ($T_J = 175\text{ }^\circ\text{C}$)

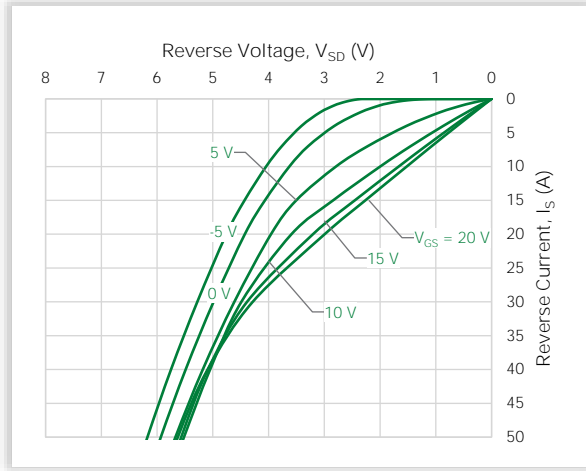


Figure 8. Typical Reverse Conduction Characteristics ($T_J = -55\text{ }^\circ\text{C}$)

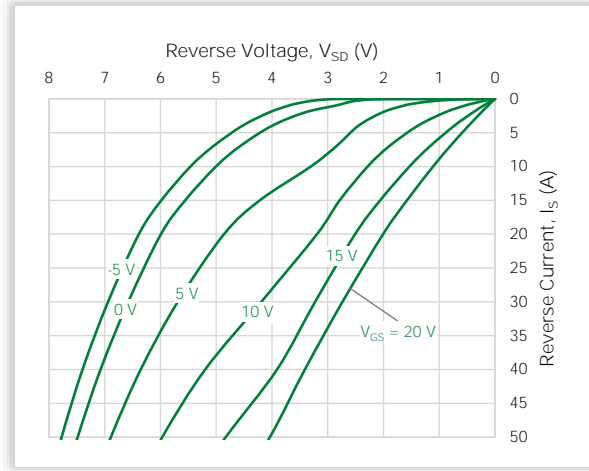


Figure 9. Transient Thermal Impedance

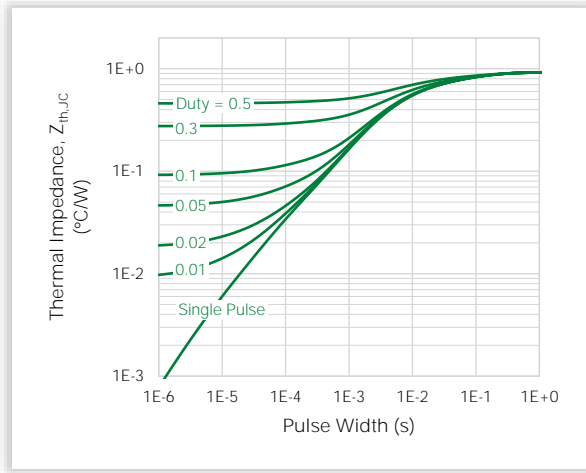


Figure 10. Maximum Safe Operating Area ($T_C = 25\text{ }^\circ\text{C}$)

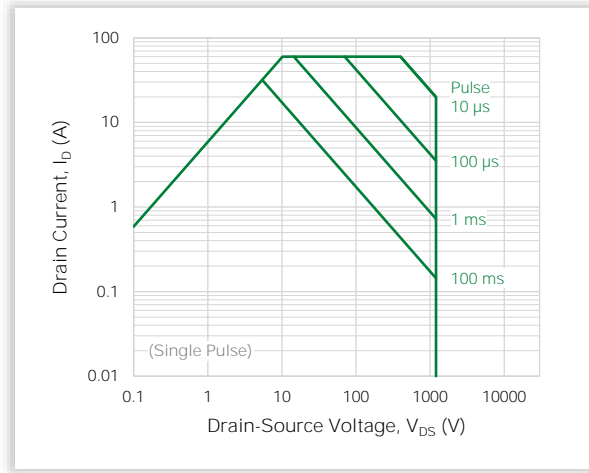


Figure 11. On-resistance vs. Drain Current

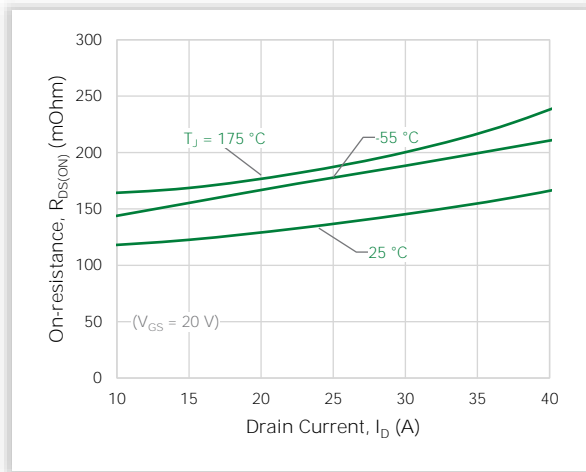


Figure 12. Normalized On-resistance vs. Junction Temperature

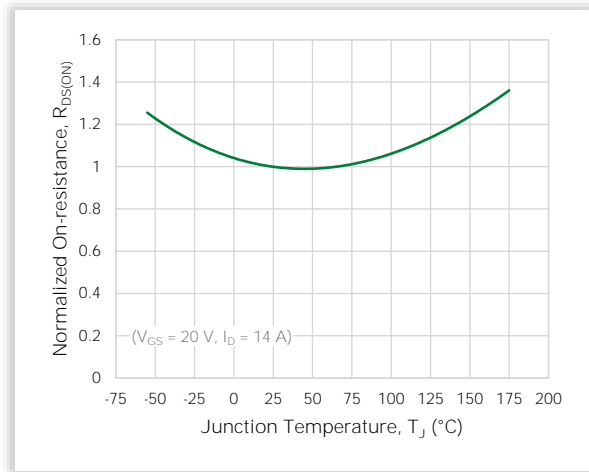


Figure 13. Typical On-resistance vs. Junction Temperature

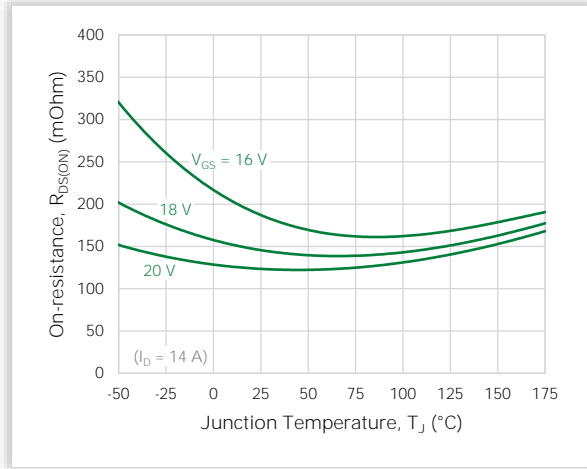


Figure 14. Typical Threshold Voltage

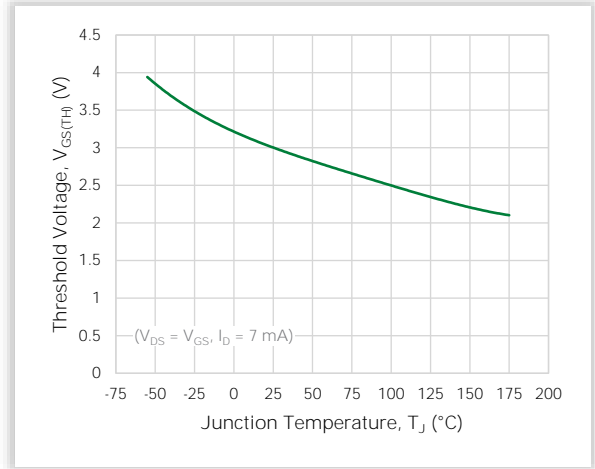


Figure 15. Typical Junction Capacitances up to 1000 V

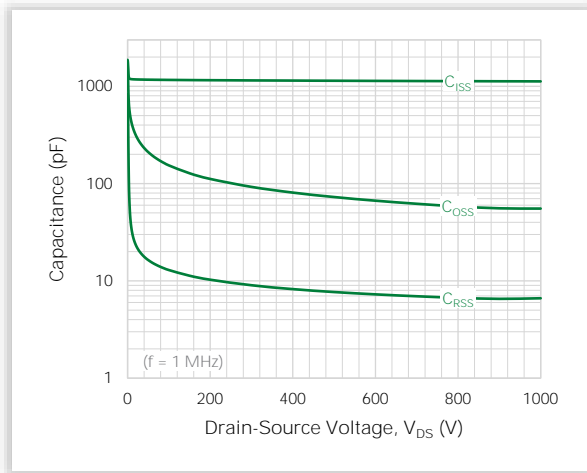


Figure 16. Typical Junction Capacitances up to 200 V

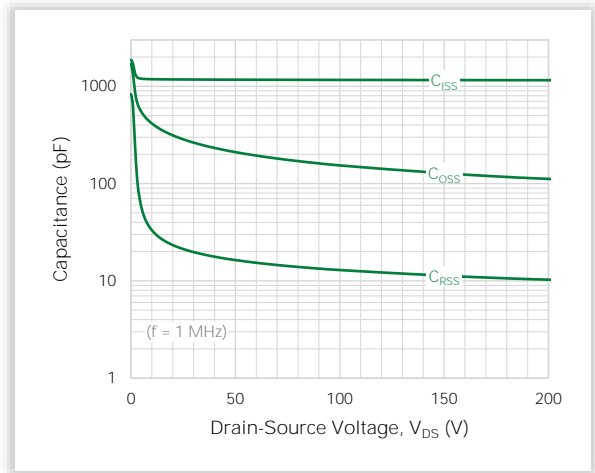


Figure 17. Typical C_{oss} Stored Energy E_{oss}

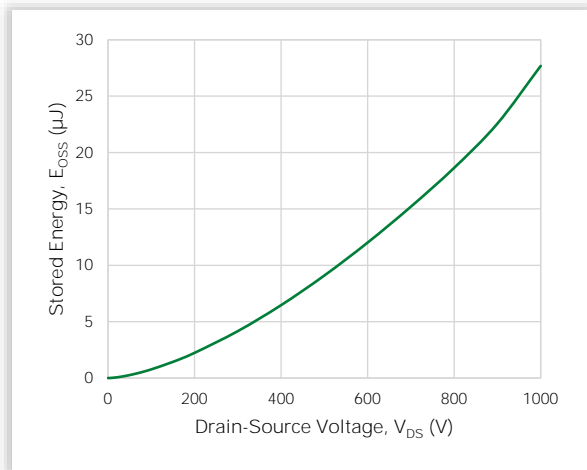


Figure 18. Typical Gate Charge

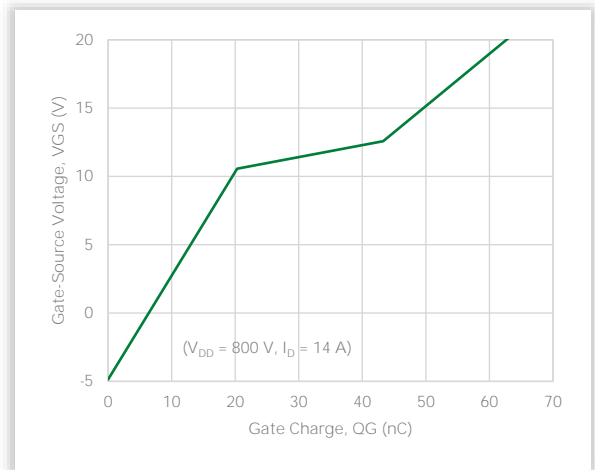


Figure 19. Typical Switching Energy vs. Drain Current

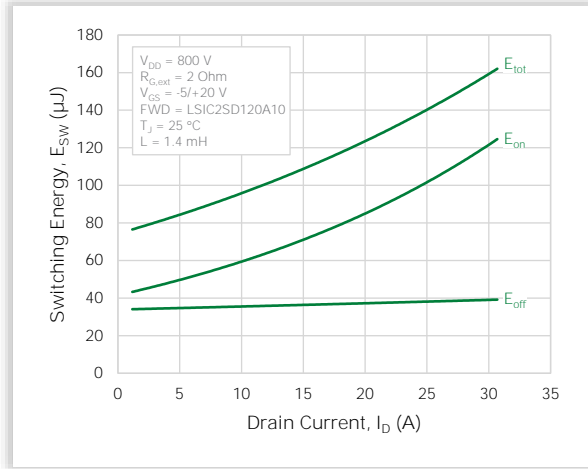


Figure 20. Typical Switching Energy vs. External Gate Resistance

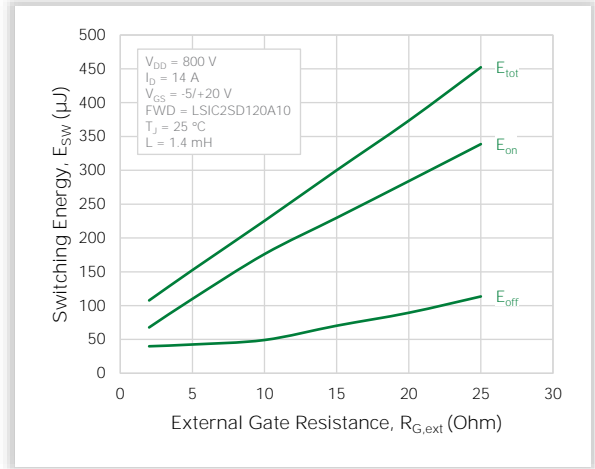
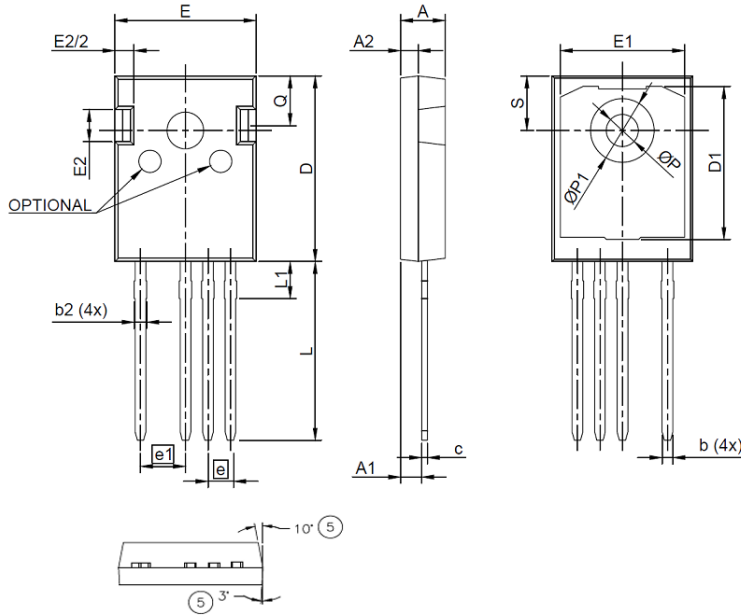


Figure 21. V_{GS} Waveform Definition

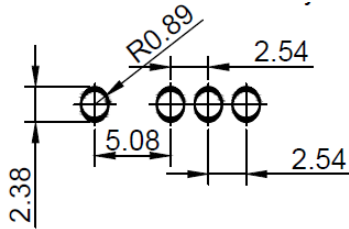


6. Package Dimensions



Symbol	Millimeters	
	Min	Max
A	4.70	5.31
A1	2.21	2.59
A2	1.50	2.49
b	0.99	1.40
b2	1.65	2.39
c	0.38	0.89
D	20.80	21.46
D1	13.08	-
D2	0.51	1.35
E	15.49	16.26
e	2.54 BSC	
e1	4.83	5.33
E1	13.46	-
E2	3.56	4.06
L	19.81	20.32
L1	-	4.50
øP	3.56	3.66
øP1	7.06	7.39
Q	5.38	6.20
S	6.17 BSC	

Recommended Hole Pattern Layout:

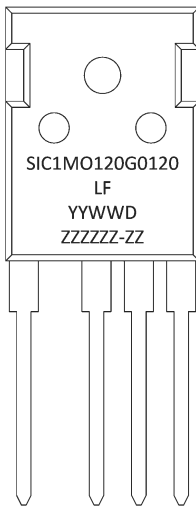


Notes:

1. Dimensioning and tolerancing as per ASME Y14.5 – 2009.
2. Package outline in compliance with JEDEC Standard Var. Ad.
3. Dimension D, E do not include mold flash.
4. Mold draft angles excluded on the table.
5. øP to have a maximum draft angle of 1.7° to the top with a maximum hole diameter of 3.912 mm.

UNIT: mm

7. Part Numbering and Marking



- SIC = SiC
- 1 = Gen 1
- MO = MOSFET
- 120 = Voltage Rating (1200 V)
- G = TO-247-4L
- 0080 = $R_{DS(ON)}$ (120 mOhm)
- YY = Year
- WW = Week
- D = Special Code
- ZZZZZZ-ZZ = Lot Number

8. Packing Options

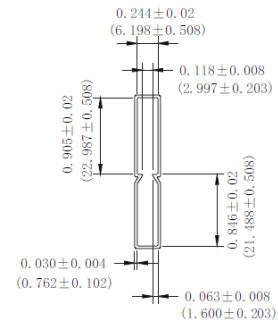
Part Number	Marking	Packing Mode	M.O.Q.
LSIC1MO120G0120	SIC1MO120G0120	Tube (30 pcs)	450

9. Packing Specifications



NOTE:

- 1. All pin plug holes are considered critical dimension
- 2. Tolerance is to be ±0.010 unless otherwise specified
- 3. Dimension are in inch (and millimeters).



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